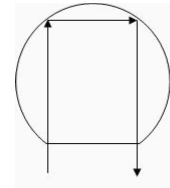
Part Number	Customer

Category		Parameter	Specification	Measurement Method
OverallWafer	1.0	Diameter	150.00 +/- 0.50 mm	Wafer Vendor
	2.0	Primary Flat Orientation	{110}+/-0.5 degree	Wafer Vendor
	3.0	Primary Flat Length	57.50 +/- 2.50 mm	Wafer Vendor
	4.0	Secondary Flat Orientation	none	
	5.0	Edge Rounding	Semi M1	Wafer Vendor
	6.0	Overall Thickness	513.00 +/- 10.00 µm	ADE, 100%
	7.0	Total Thickness Variation (TTV)	<3.00µm	Guaranteed by Process
	9.0	Bow	<50.00µm	ADE to ASTM F534, 20%
	10.0	Warp	<50.00µm	ADE to ASTM F657, 20%
	11.0	Edge Chips	0	Bright Light, 100% (note 2)
	12.0	Edge Exclusion	5mm	
HandleSilicon	13.0	Handle Growth Method	CZ or FZ	Wafer Vendor
	14.0	Handle Orientation	{100} +/- 1 degree	Wafer Vendor
	15.0	Handle Doping Type	N or P	Wafer Vendor
	16.0	Handle Dopant	ANY	Wafer Vendor
	17.0	Handle Resistivity	1 - 1000 Ohmcm	Wafer Vendor
	18.0	Handle Thickness	500.00 +/- 10.00 um	ADE, 100%inspection
	19.0	Backside Finish	ANY Sacraficial layer	Guaranteed by Process
BuriedOxide	20.0	Oxide formed on	Both handle and device	
	21.0	Oxide Thickness	10,000.00 +/- 1,000.00 A	
DeviceSilicon	31.0	Device Growth Method	CZ	Wafer Vendor
	32.0	Device Orientation	{100} +/- 0.5 degree	Wafer Vendor
	33.0	Device Doping Type	N	Wafer Vendor
	34.0	Device Dopant	Phosphorous	Wafer Vendor
	35.0	Device Resistivity	1 - 3 Ohmcm	Wafer Vendor
	36.0	Nominal Thickness	11.75 +/- 0.75 um	FTIR or Filmetrics 9 point measurement
	37.0	Distance to device silicon edge from wafer edge	<2mm	Guaranteed by process
	39.0	Voids	none inside 5mm edge exclusion	Bright Light inspection 100%
	40.0	Scratches	none	Bright Light inspection 100%
	41.0	Haze	none	Bright Light inspection

Part Number	Customer		
Category	**Parameter**	**Specification**	**Measurement Method**
Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	

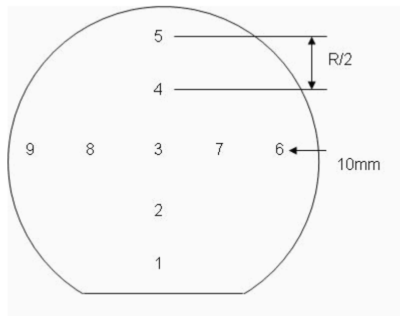
Explanatory Notes

1. Microscope inspection performed using microscope scan as below. 5x objective.



2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information